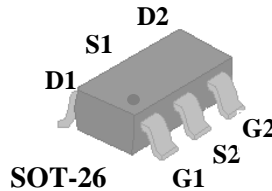




- ▼ Low Gate Charge Drive
- ▼ Low On-resistance
- ▼ Surface Mount Package
- ▼ RoHS Compliant & Halogen-Free

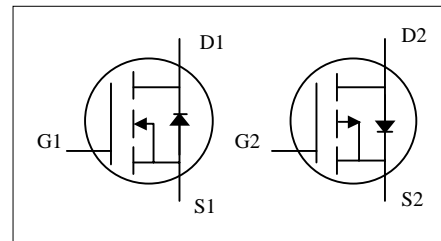


N-CH	BV_{DSS}	16V
	$R_{DS(ON)}$	58m Ω
	I_D	3.5A
P-CH	BV_{DSS}	-16V
	$R_{DS(ON)}$	125m Ω
	I_D	-2.5A

Description

Advanced Power MOSFETs utilized advanced processing techniques to achieve the lowest possible on-resistance, extremely efficient and cost-effectiveness device.

The SOT-26 package is widely used for all commercial-industrial applications.



Absolute Maximum Ratings

Symbol	Parameter	Rating		Units
		N-channel	P-channel	
V_{DS}	Drain-Source Voltage	16	-16	V
V_{GS}	Gate-Source Voltage	± 8	± 8	V
$I_D@T_A=25^\circ C$	Continuous Drain Current ³	3.5	-2.5	A
$I_D@T_A=70^\circ C$	Continuous Drain Current ³	2.8	-2	A
I_{DM}	Pulsed Drain Current ¹	10	-10	A
$P_D@T_A=25^\circ C$	Total Power Dissipation	1.14		W
	Linear Derating Factor	0.01		W/ $^\circ C$
T_{STG}	Storage Temperature Range	-55 to 150		$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150		$^\circ C$

Thermal Data

Symbol	Parameter	Value	Unit
Rthj-a	Maximum Thermal Resistance, Junction-ambient ³	110	$^\circ C/W$



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N-CH Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	16	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance ²	V _{GS} =4.5V, I _D =3A	-	-	58	mΩ
		V _{GS} =2.5V, I _D =2A	-	-	70	mΩ
		V _{GS} =1.8V, I _D =1A	-	-	85	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250uA	0.2	-	1	V
g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =3A	-	9	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =16V, V _{GS} =0V	-	-	1	uA
	Drain-Source Leakage Current (T _j =70°C)	V _{DS} =12V, V _{GS} =0V	-	-	25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±8V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =3A V _{DS} =10V V _{GS} =4.5V	-	7	12	nC
Q _{gs}	Gate-Source Charge		-	0.6	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge		-	2	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =10V I _D =1A R _G =3.3Ω V _{GS} =5V	-	6	-	ns
t _r	Rise Time		-	11	-	ns
t _{d(off)}	Turn-off Delay Time		-	17	-	ns
t _f	Fall Time		-	3	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V V _{DS} =10V f=1.0MHz	-	365	585	pF
C _{oss}	Output Capacitance		-	70	-	pF
C _{rss}	Reverse Transfer Capacitance		-	60	-	pF
R _g	Gate Resistance	f=1.0MHz	-	1.4	2	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V _{SD}	Forward On Voltage ²	I _S =0.9A, V _{GS} =0V	-	-	1.3	V



P-CH Electrical Characteristics @T_j=25°C(unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250uA	-16	-	-	V
R _{DS(ON)}	Static Drain-Source On-Resistance	V _{GS} =-4.5V, I _D =-2A	-	-	125	mΩ
		V _{GS} =-2.5V, I _D =-1.6A	-	-	165	mΩ
		V _{GS} =-1.8V, I _D =-1A	-	-	210	mΩ
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =-250uA	-0.2	-	-1	V
g _{fs}	Forward Transconductance	V _{DS} =-5V, I _D =-2A	-	5	-	S
I _{DSS}	Drain-Source Leakage Current	V _{DS} =-16V, V _{GS} =0V	-	-	-1	uA
	Drain-Source Leakage Current (T _j =70°C)	V _{DS} =-12V, V _{GS} =0V	-	-	-25	uA
I _{GSS}	Gate-Source Leakage	V _{GS} =±8V, V _{DS} =0V	-	-	±100	nA
Q _g	Total Gate Charge ²	I _D =-2A	-	6	10	nC
Q _{gs}	Gate-Source Charge	V _{DS} =-10V	-	0.8	-	nC
Q _{gd}	Gate-Drain ("Miller") Charge	V _{GS} =-4.5V	-	2	-	nC
t _{d(on)}	Turn-on Delay Time ²	V _{DS} =-10V	-	7	-	ns
t _r	Rise Time	I _D =-1A	-	20	-	ns
t _{d(off)}	Turn-off Delay Time	R _G =3.3Ω	-	23	-	ns
t _f	Fall Time	V _{GS} =-5V	-	24	-	ns
C _{iss}	Input Capacitance	V _{GS} =0V	-	380	610	pF
C _{oss}	Output Capacitance	V _{DS} =-10V	-	90	-	pF
C _{rss}	Reverse Transfer Capacitance	f=1.0MHz	-	75	-	pF
R _g	Gate Resistance	f=1.0MHz	-	8	12	Ω

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{SD}	Forward On Voltage ²	I _S =-0.9A, V _{GS} =0V	-	-	-1.3	V

Notes:

- 1.Pulse width limited by Max. junction temperature.
- 2.Pulse test
- 3.Surface mounted on 1 in² copper pad of FR4 board, t_{sec}≤5sec ; 180°C/W when mounted on min. copper pad.

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

APEC DOES NOT ASSUME ANY LIABILITY ARISING OUT OF THE APPLICATION OR USE OF ANY PRODUCT OR CIRCUIT DESCRIBED HEREIN; NEITHER DOES IT CONVEY ANY LICENSE UNDER ITS PATENT RIGHTS, NOR THE RIGHTS OF OTHERS.

APEC RESERVES THE RIGHT TO MAKE CHANGES WITHOUT FURTHER NOTICE TO ANY PRODUCTS HEREIN TO IMPROVE RELIABILITY, FUNCTION OR DESIGN.



N-Channel

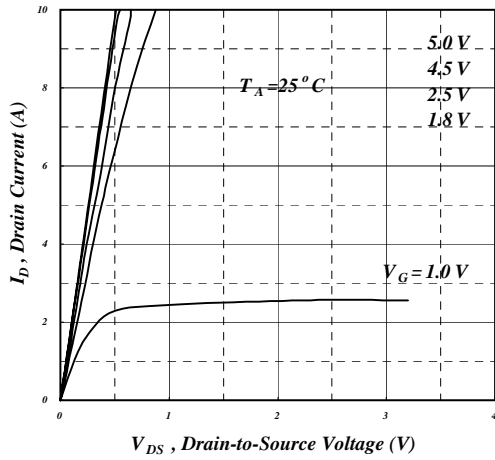


Fig 1. Typical Output Characteristics

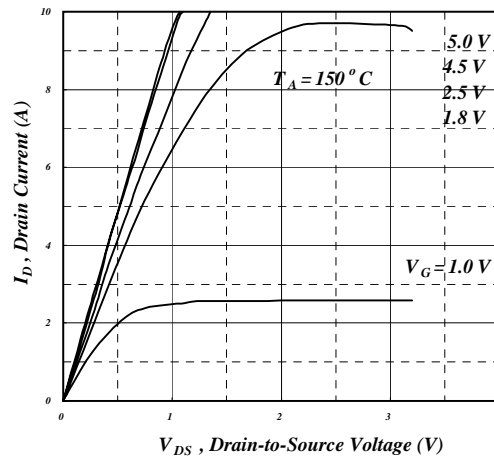


Fig 2. Typical Output Characteristics

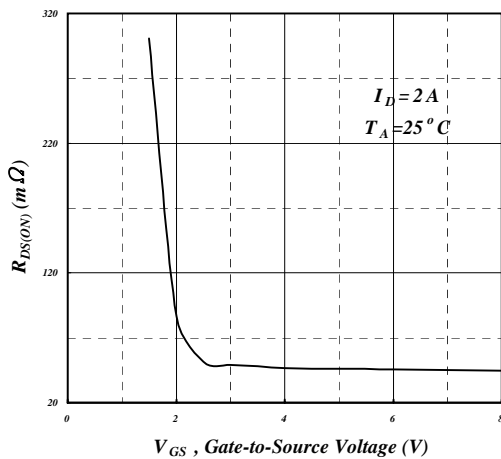


Fig 3. On-Resistance v.s. Gate Voltage

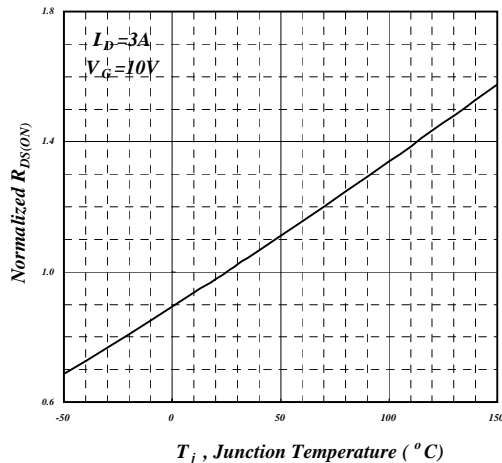


Fig 4. Normalized On-Resistance v.s. Junction Temperature

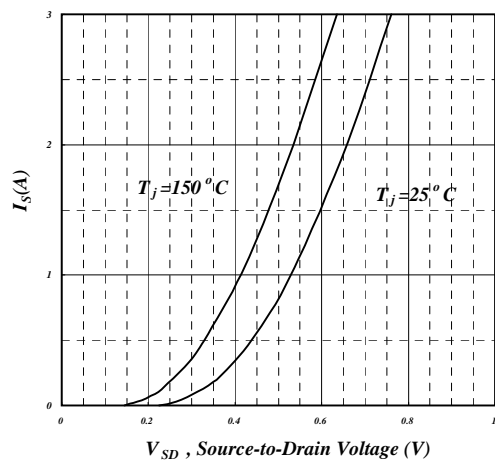


Fig 5. Forward Characteristic of Reverse Diode

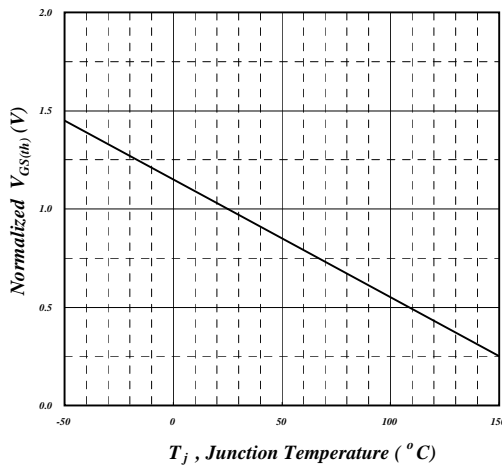


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



N-Channel

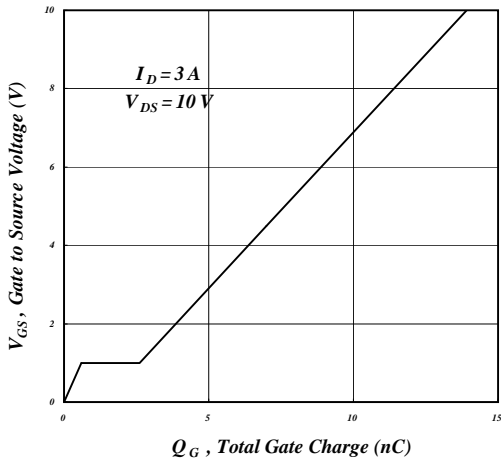


Fig 7. Gate Charge Characteristics

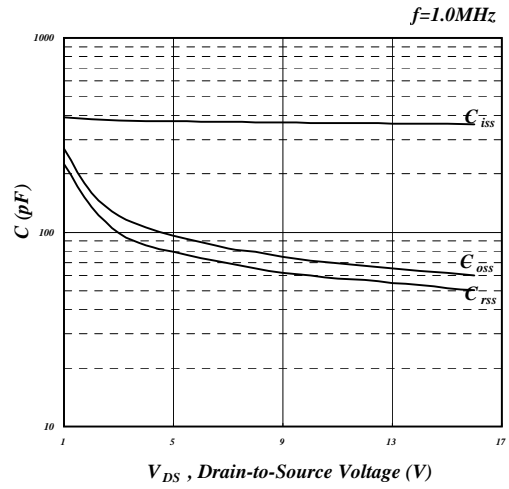


Fig 8. Typical Capacitance Characteristics

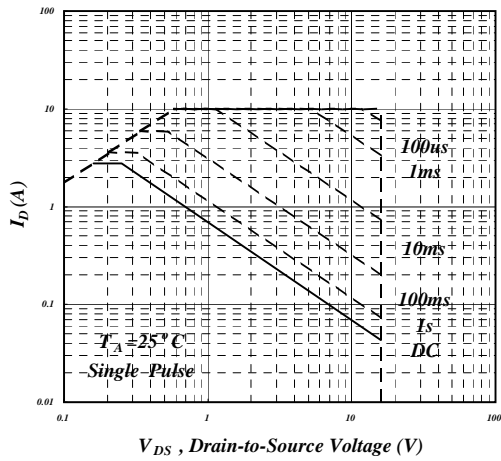


Fig 9. Maximum Safe Operating Area

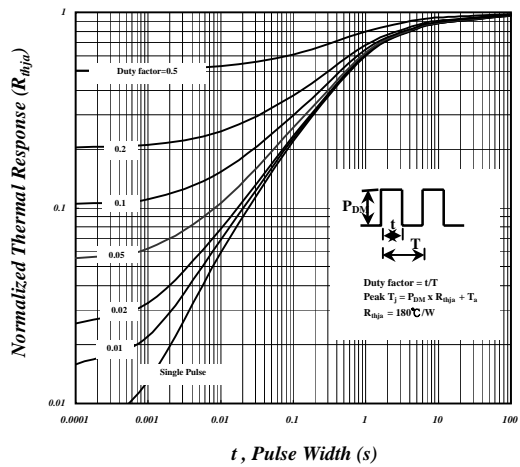


Fig 10. Effective Transient Thermal Impedance

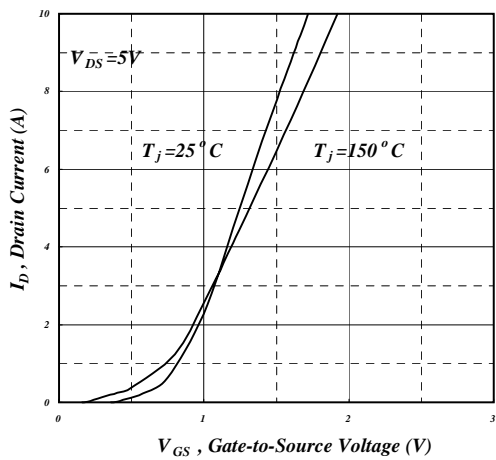


Fig 11. Transfer Characteristics

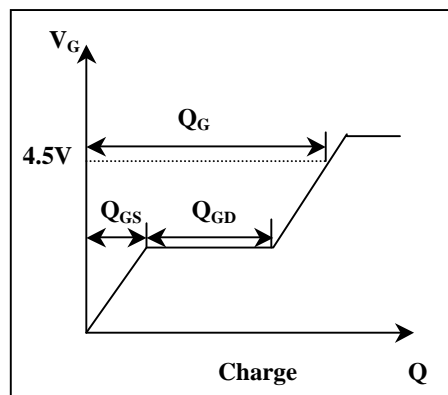


Fig 12. Gate Charge Waveform



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P-Channel

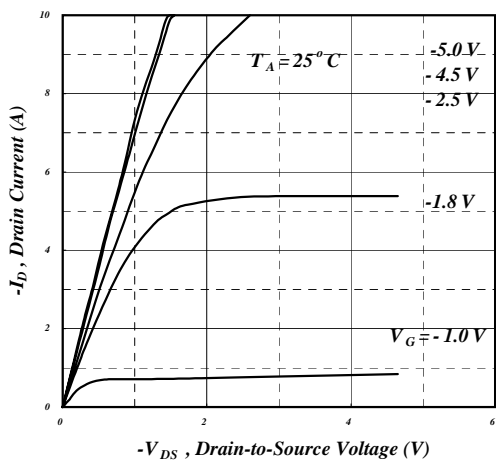


Fig 1. Typical Output Characteristics

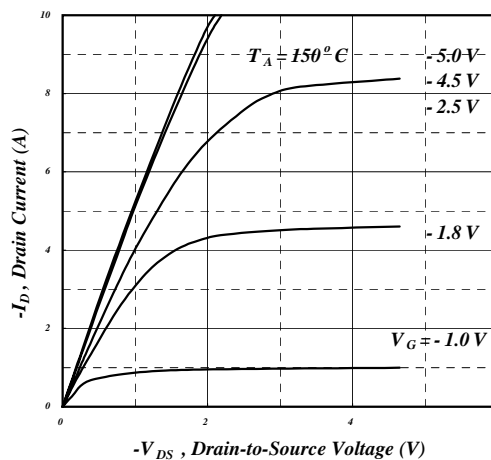


Fig 2. Typical Output Characteristics

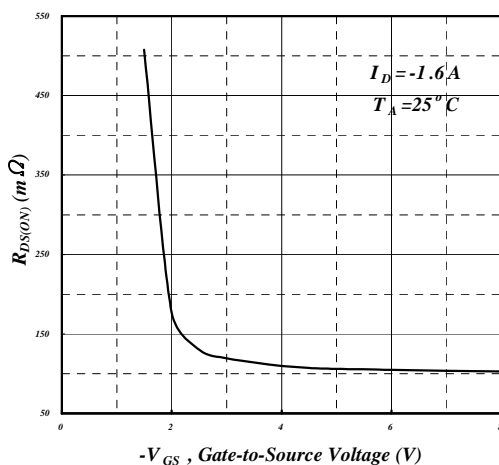


Fig 3. On-Resistance v.s. Gate Voltage

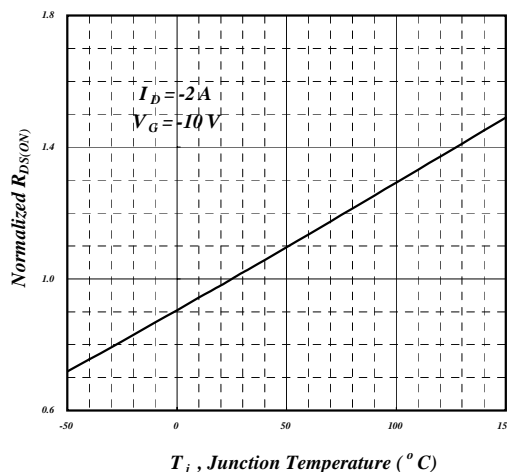


Fig 4. Normalized On-Resistance v.s. Junction Temperature

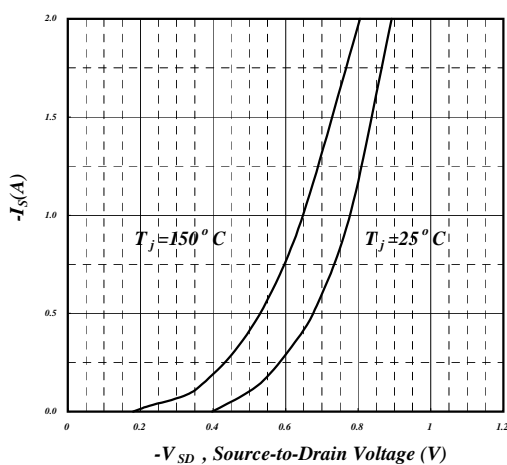


Fig 5. Forward Characteristic of Reverse Diode

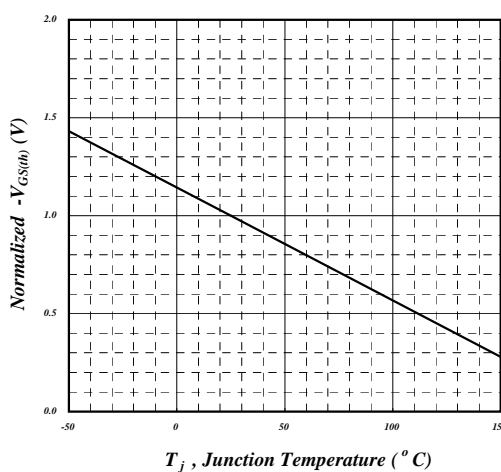


Fig 6. Gate Threshold Voltage v.s. Junction Temperature



P-Channel

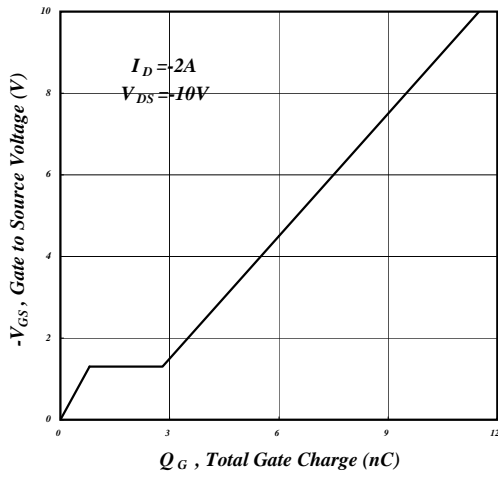


Fig 7. Gate Charge Characteristics

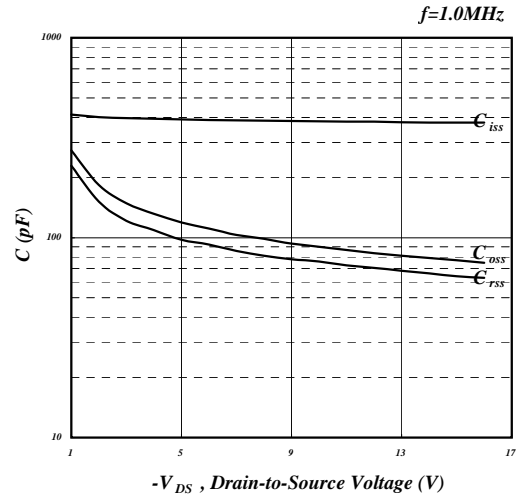


Fig 8. Typical Capacitance Characteristics

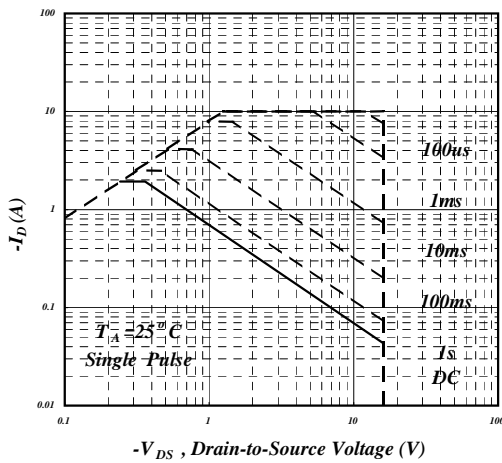


Fig 9. Maximum Safe Operating Area

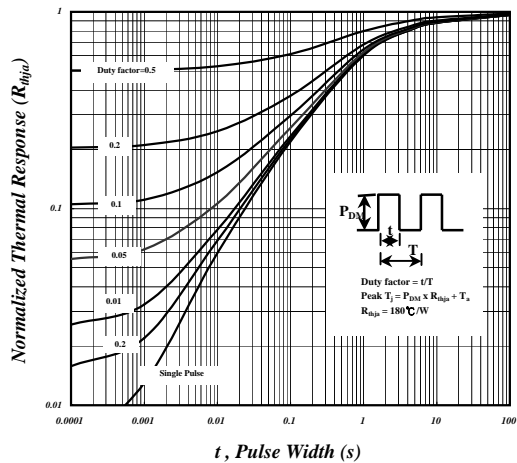


Fig 10. Effective Transient Thermal Impedance

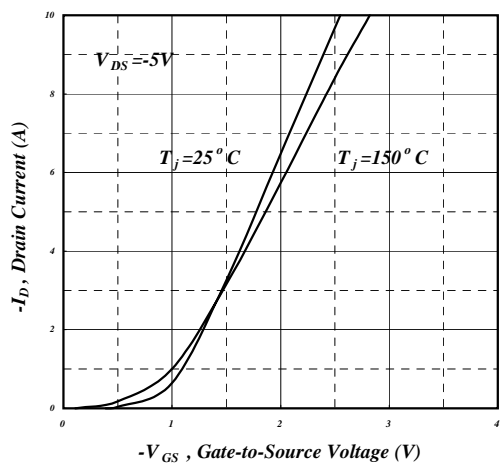


Fig 11. Transfer Characteristics

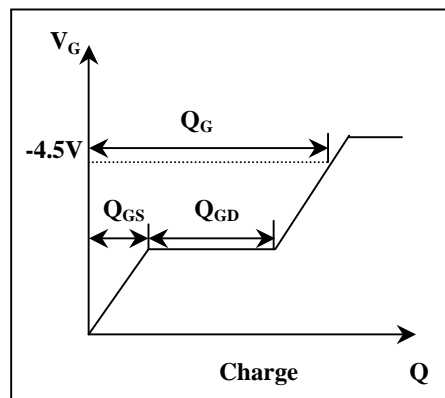


Fig 12. Gate Charge Waveform